

L Number	Hits	Search Text	DB	Time stamp
2	0	("densified dielectric").PN.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 16:18
7	0	("densified").PN.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:15
12	0	("densified").PN.	USPAT	2002/07/18 17:15
13	8939	densification	USPAT	2002/07/18 17:15
14	71	densification near dielectric	USPAT	2002/07/18 17:16
15	616	densification same dielectric	USPAT	2002/07/18 17:15
16	25	(densification near dielectric) and plasma	USPAT	2002/07/18 17:22
17	697	"low k dielectric"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:23
22	105	"low k dielectric" same "etch stop"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:38
27	1	6054379.pn.	USPAT	2002/07/18 17:48
28	271	treat\$3 near dielectric	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:49
33	87	(treat\$3 near dielectric) and plasma	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:53
38	11	((treat\$3 near dielectric) and plasma) and "etch stop"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:56
43	2	5314845.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 17:58
48	2	5915203.pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:00
53	2	("6303047" "6365528").pn.	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
58	44591	silicon with carbide	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:06
63	42528	silicon with carbon	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
68	73891	(silicon with carbide) or (silicon with carbon)	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:07
73	19286	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen)	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:09
78	189	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen) and "low k"	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10
83	167	((silicon with carbide) or (silicon with carbon)) same (plasma densified plasma Hydrogen He Helium Ar Argon NH3 ammonia N2 nitrogen) and "low k") and etch\$3	USPAT; US-PGPUB; EPO; JPO	2002/07/18 18:10